L Number	Hits	Search Text	DB	Time stamp
-	768	(semiconductor near laser) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (mirror or ((low and high) near reflect$)) and 372/$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/14 16:26
-	260	((semiconductor near laser) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (mirror or ((low and high) near reflect$)) and 372/$) and 372/96	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/11/29 18:04
-	11	(((semiconductor near laser) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (mirror or ((low and high) near reflect$)) and 372/$) and 372/96) and (laminat$ near structure)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/11/29 18:05
-	4	(semiconductor near laser) and (active near (layer or region or medium or film)) and (quantum near well or qw) and ((low and high) near reflect$) and 372/$ and (laminat$ near structure)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/14 16:28
-	4	((semiconductor near laser) and (active near (layer or region or medium or film) SAME (quantum near well or qw)) and ((low and high) near reflect$) and (laminat$ near structure)) and 372/$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/11/29 18:19
-	5	(semiconductor near laser) and (active near (layer or region or medium or film) SAME (quantum near well or qw)) and ((low and high) near reflect$) and (laminat$ near structure)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/11/29 19:24
-	73	(semiconductor near laser) and (active near (layer or region or medium or film) SAME (quantum near well or qw)) and ((low and high) near reflect$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/11/29 19:27
-	1	(semiconductor near laser) and (active near (layer or region or medium or film) SAME (quantum near well or qw)) and ((low and high) near mirror) and (laminat$ near structure)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/11/29 19:27
-	56	((semiconductor near laser) and (active near (layer or region or medium or film) SAME (quantum near well or qw)) and ((low and high) near reflect$)) and 372/$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/11/29 19:28
-	4	(semiconductor near laser) and (active near (layer or region or medium or film) SAME (quantum near well or qw)) and ((low and high) near mirror)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/11/29 19:42
-	1093	(semiconductor near laser) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (mirror or ((low and high) near reflect$)) and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/14 16:36
-	186	(semiconductor near laser) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (low near reflect$5)and (high near reflect$5) and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/14 16:48

-	113	((semiconductor near laser) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (low near reflect$5)and (high near reflect$5) and substrate) and cavity	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/14 17:25
-	63	((semiconductor near laser) and (active near (layer or region or medium or film)) and (quantum near well or qw) and (low near reflect$5)and (high near reflect$5) and substrate) and (cavity near2 length)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/14 17:26
-	43	((semiconductor near laser) with (optical near fiber)) and (active near (layer or region or medium or film)) and (quantum near well or qw) and ((low and high) near reflect$) and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/16 15:26